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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

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Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	28
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 9x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	40-WFQFN Exposed Pad
Supplier Device Package	40-HWQFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101egdna-u0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Flash	Data	RAM			RL78	/G13		
ROM	flash		20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128	8 KB	12	_	_	_	R5F100AG	R5F100BG	R5F100CG
KB	-	KB	_	_	_	R5F101AG	R5F101BG	R5F101CG
96	8 KB	8 KB	-	-	-	R5F100AF	R5F100BF	R5F100CF
KB	-		_	_	-	R5F101AF	R5F101BF	R5F101CF
64	4 KB	4 KB	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
KB	-	Note	R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
KB	_		R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
KB	-		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16 KB	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
KB	_		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

O ROM, RAM capacities

		1								1
Flash	Data	RAM				RL78	3/G13			
ROM	flash		40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512	8 KB	32 KB	_	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
KB	_	Note	-	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384	8 KB	24 KB	_	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
KB	-		-	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256	8 KB	20 KB	-	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
KB	-	Note	-	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
KB	1		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	_
KB	-		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	-
96	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	-
KB	-		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	-
64	4 KB	4 KB	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	-	-	-
KB	-	Note	R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	-	-	-
48	4 KB	3 KB ^{Note}	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	-	-	_
KB	_		R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	-	-	-
32	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	-	_	_
KB	_	1	R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	-	-	-
16	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	-	-	-	-	-
KB	-		R5F101EA	R5F101FA	R5F101GA	-	-	-	_	-

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H

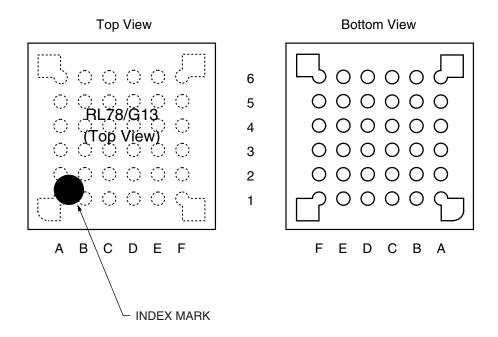
R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address FAF00H Start address F7F00H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).



1.3.6 36-pin products

• 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



	А	В	С	D	E	F	_
	P60/SCLA0	Vdd	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	
6							6
	P62	P61/SDAA0	Vss	REGC	RESET	P120/ANI19	
5							5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/(SCLA0) /(TI03)/(TO03)	P31/TI03/TO03/ INTP4/ PCLBUZ0	P00/TI00/TxD1	P01/TO00/RxD1	4
3	P50/INTP1/ SI11/SDA11	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ (TI02)/(TO02)	P22/ANI2	P20/ANI0/ AVrefp	P21/ANI1/ AVREFM	3
2	P30/INTP3/ SCK11/SCL11	P16/TI01/TO01/ INTP5/(RxD0)	P12/SO00/ TxD0/TOOLTxD /(TI05)/(TO05)	P11/SI00/RxD0/ TOOLRxD/ SDA00/(TI06)/ (TO06)	P24/ANI4	P23/ANI3	2
1	P51/INTP2/ SO11	P17/TI02/TO02/ (TxD0)	P13/TxD2/ SO20/(SDAA0)/ (TI04)/(TO04)	P10/SCK00/ SCL00/(TI07)/ (TO07)	P147/ANI18	P25/ANI5	1
	А	В	С	D	E	F	

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

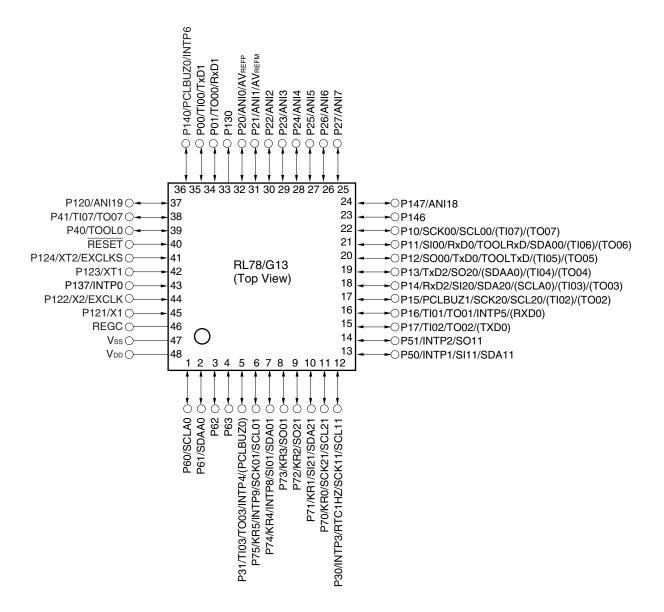
Remarks 1. For pin identification, see 1.4 Pin Identification.

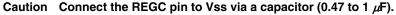
Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



1.3.9 48-pin products

• 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)





Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

	Item	20-p	oin	24-	pin	25	-pin	30-	pin	32-	pin	(1/2 36-	pin
		, ד	Ъ	Я	גר	д	גר	Ъ	דג	Ъ	ភ្ល	Ъ	
		5F1	5F1	5F10	5F10	5F10	5F10	5F10	5F10	5F10	5F10	5F10	5F1(
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Code flash me	emory (KB)	16 to	64	16 t	o 64	161	o 64	16 to	128		128	16 to	128
Data flash me	emory (KB)	4	_	4	_	4	_	4 to 8	_	4 to 8	_	4 to 8	_
RAM (KB)		2 to 4	Note1	2 to	4 ^{Note1}	2 to	4 ^{Note1}	2 to ⁻	12 ^{Note1}	2 to 1	2 ^{Note1}	2 to ⁻	2 ^{Note1}
Address spac	e	1 MB		•		L							
Main system clock	High-speed system clock	X1 (crys HS (High HS (High LS (Low LV (Low	n-speed n-speed -speed	l main) m l main) m main) m	node: 1 t node: 1 t ode: 1 to	o 20 MH o 16 MH o 8 MHz	Iz (V _{DD} = Iz (V _{DD} = (V _{DD} = 1.	2.7 to 5. 2.4 to 5. 8 to 5.5	.5 V), .5 V), V),	EXCLK)			
	High-speed on-chip oscillator	HS (High LS (Low	HS (High-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)										
Subsystem cl	ock												
Low-speed or	n-chip oscillator	15 kHz (TYP.)										
General-purp	ose registers	(8-bit register × 8) × 4 banks											
Minimum inst	ruction execution time	0.03125	μs (Hig	h-speed	on-chip	oscillato	or: fін = 3	2 MHz o	peration)			
		0.05 μs ((High-sp	beed sys	tem cloo	ck: fмx =	20 MHz	operatio	n)				
Instruction set		 Data ti Adder Multipli Rotate 	and su lication	btractor/ (8 bits ×	logical o 8 bits)				t, and B	oolean o	peration), etc.	
I/O port	Total	16 20 21 26 28 32							2				
	CMOS I/O	13 (N-ch O [V₀₀ with voltage	.D. I/O nstand	(N-ch C	thstand	(N-ch ([V _{DD} w	5 D.D. I/O thstand ge]: 6)	2 (N-ch C [V⊳⊳ wi voltag	D.D. I/O thstand	2 (N-ch C [V _{DD} wi [*] voltag	D.D. I/O thstand	2 (N-ch C [V _{DD} wi voltag	D.D. I/C
	CMOS input	3		:	3		3	:	3	3	3	3	3
	CMOS output	-		-	-		1	-	-	-	-	-	-
	N-ch O.D. I/O (withstand voltage: 6 V)	-		2	2		2	2	2	3	3	3	3
Timer	16-bit timer						8 cha	nnels					
	Watchdog timer						1 cha	nnel					
	Real-time clock (RTC)						1 chan	nel Note 2					
	12-bit interval timer (IT)						1 cha	nnel					
	Timer output	3 channe (PWM ou 2 ^{№0€ 3})		4 chanr (PWM	nels outputs:	3 ^{Note 3})			``	M output M output	,		
	RTC output			•				-					
Notes 1.	The flash library us The target products R5F100xD, R5F R5F100xE, R5F For the RAM areas for RL78 Family (I Only the constant	s and sta 101xD (: 101xE () used by R20UT29	$\begin{array}{l} \text{rt addr} \\ x = 6 \text{ to} \\ x = 6 \text{ to} \\ \text{r the flate} \\ \textbf{944}. \end{array}$	ress of t o 8, A to o 8, A to ash libra	he RAN o C): S o C): S ury, see	A areas Start add Start add Start add Self R	used by dress Ff dress Ff AM list	y the fla F300H EF00H of Flas	sh libra h Self-	ry are s Progra i	hown b mming	Library	

^{2.} Only the constant-period interrupt function when the low-speed on-chip oscillator clock (fiL) is selected



 The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

^{3.} When setting to PIOR = 1

lt a	m	40	nin	11	nin	10	nin	EO	nin	64	(2) nin
Ite		40-			-pin		-pin	52	-pin I		-pin
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Clock output/buzz	er output	:	2		2		2		2		2
·		(Main s • 256 Hz	system clo z, 512 Hz,	оск: fмаin = 1.024 kHz	20 MHz c z, 2.048 kH	. ,	Hz, 8.192		884 kHz, 32	2.768 kHz	
8/10-bit resolution	A/D converter	9 channels 10 channels 10 channels 12 channels 12 channels									
Serial interface		[40-pin, 44-pin products]									
		 CSI: 1 CSI: 2 [48-pin, 5 CSI: 2 CSI: 1 CSI: 2 [64-pin pi CSI: 2 CSI: 2 CSI: 2 	channel/s channels/ 2-pin proo channels/ channels/ roducts] channels/ channels/ channels/	implified I ² simplified ducts] simplified I ² simplified I ² simplified simplified	C: 1 chani I ² C: 2 chai I ² C: 2 chai C: 1 chani I ² C: 2 chai I ² C: 2 chai I ² C: 2 chai	nnels/UAR nel/UART: nnels/UAR nnels/UAR nnels/UAR	1 channe T (UART : 1 channe T (UART : T (UART : T: 1 chann T: 1 chann	l supporting nel l supporting nel	g LIN-bus): g LIN-bus): g LIN-bus):	1 channel	I
	I ² C bus	1 channe		1 channe		1 channe		1 channe		1 channe	
Multiplier and divid		 16 bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 									
		• 16 bits	× 16 bits +	- 32 bits =	32 bits (U	nsigned or	r signed)				
DMA controller		2 channe	ls								
Vectored	Internal	2	27	:	27	2	27		27	2	27
interrupt sources	External		7		7		10		12		13
Key interrupt			4		4		6		8		8
Reset		 Interna Interna Interna Interna Interna 	I reset by I reset by I reset by I reset by	watchdog power-on- voltage de	reset etector ruction ex sy error	ecution ^{Note}					
Power-on-reset ci	rcuit		on-reset: down-res	1.51 V et: 1.50 V	. ,						
Voltage detector		Rising edge : 1.67 V to 4.06 V (14 stages) Falling edge : 1.63 V to 3.98 V (14 stages)									
On-chip debug fur	nction	Provided									
Power supply volta				$T_A = -40 \text{ to}$ $T_A = -40 \text{ to}$							
Operating ambien	$T_A = 40 to$	o +85°C (/		ner applica	itions, D: Ii ations)	ndustrial a	pplication	s)			

<R>

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.



2.3 DC Characteristics

2.3.1 Pin characteristics

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$1.6~V \leq EV_{DD0} \leq 5.5~V$			-10.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			-55.0	mA
		P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-10.0	mA
		$(\text{When duty} \le 70\%^{\text{Note 3}})$	$1.8~V \leq EV_{\text{DD0}} < 2.7~V$			-5.0	mA
			$1.6~V \leq EV_{\text{DD0}} < 1.8~V$			-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31,				-80.0	mA
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-19.0	mA
		P117, P146, P147	$1.8~V \leq EV_{\text{DD0}} < 2.7~V$			-10.0	mA
		(When duty \leq 70% ^{Note 3})	$1.6~V \leq EV_{\text{DD0}} < 1.8~V$			-5.0	mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})	$1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$			-135.0 Note 4	mA
	Іон2	Per pin for P20 to P27, P150 to P156	$1.6~V \leq V_{\text{DD}} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})	$1.6~V \leq V_{\text{DD}} \leq 5.5~V$			-1.5	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.

- 2. However, do not exceed the total current value.
- **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- **4.** The applied current for the products for industrial application (R5F100xxDxx, R5F101xxDxx, R5F100xxGxx) is -100 mA.
- Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

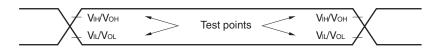
(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD2	HALT	HS (high-	$f_{IH} = 32 \text{ MHz}^{Note 4}$	VDD = 5.0 V		0.62	1.89	mA
Current	Note 2	mode	speed main) mode ^{Note 7}		V _{DD} = 3.0 V		0.62	1.89	mA
			mode	fiH = 24 MHz ^{Note 4}	VDD = 5.0 V		0.50	1.48	mA
					VDD = 3.0 V		0.50	1.48	mA
				fi⊢ = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.12	mA
					V _{DD} = 3.0 V		0.44	1.12	mA
			LS (low-	fiH = 8 MHz ^{Note 4}	$V_{DD} = 3.0 V$		290	620	μA
			speed main) mode ^{Note 7}		$V_{DD} = 2.0 V$		290	620	μA
			LV (low-	fin = 4 MHz ^{Note 4}	VDD = 3.0 V		460	700	μA
			voltage main) mode		V _{DD} = 2.0 V		460	700	μA
			HS (high-	fмx = 20 MHz ^{Note 3} ,	Square wave input		0.31	1.14	mA
			speed main) mode ^{Note 7}	V _{DD} = 5.0 V	Resonator connection		0.48	1.34	mA
				$f_{MX} = 20 \text{ MHz}^{Note 3}$,	Square wave input		0.31	1.14	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.48	1.34	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3}$,	Square wave input		0.21	0.68	mA
				$V_{DD} = 5.0 V$	Resonator connection		0.28	0.76	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	0.68	mA
			Vdd = 3.0 V	Resonator connection		0.28	0.76	mA	
			LS (low-	f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		110	390	μA
			speed main) mode ^{Note 7}	Vdd = 3.0 V	Resonator connection		160	450	μA
				f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		110	390	μA
				VDD = 2.0 V	Resonator connection		160	450	μA
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.31	0.66	μA
			clock operation	$T_A = -40^{\circ}C$	Resonator connection		0.50	0.85	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.38	0.66	μA
				T _A = +25°C	Resonator connection		0.57	0.85	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.47	3.49	μA
				$T_A = +50^{\circ}C$	Resonator connection		0.66	3.68	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.80	6.10	μA
				T _A = +70°C	Resonator connection		0.99	6.29	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		1.52	10.46	μA
				$T_A = +85^{\circ}C$	Resonator connection		1.71	10.65	μA
	$I_{DD3}^{Note 6} STOP T_{A} = -40$	$T_A = -40^{\circ}C$	1	1	1	0.19	0.54	μA	
		mode ^{Note 8}	T _A = +25°C			1	0.26	0.54	μA
			T _A = +50°C				0.35	3.37	μA
			$T_{A} = +70^{\circ}C$				0.68	5.98	μΑ
			T _A = +85°C			+	1.40	10.34	μΑ

(Notes and Remarks are listed on the next page.)

2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode) (T_A = -40 to +85°C, 1.6 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol		Conditions	、 U	h-speed Mode	``	/-speed Mode	``	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.4 V≤ EV	5.5 V		fMCK/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		5.3		1.3		0.6	Mbps
		1.8 V ≤ EV	$T_{\text{DD0}} \leq 5.5 \text{ V}$		fмск/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		5.3		1.3		0.6	Mbps
		1.7 V ≤ EV	$T_{\text{DD0}} \leq 5.5 \text{ V}$		fMCK/6 Note 2		fмск/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		5.3		1.3		0.6	Mbps
		1.6 V ≤ EV	$T_{\text{DD0}} \leq 5.5 \text{ V}$	_	_		fмск/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$	_	_		1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$.

 $2.4~V \leq EV_{\text{DD0}}$ < 2.7 V : MAX. 2.6 Mbps

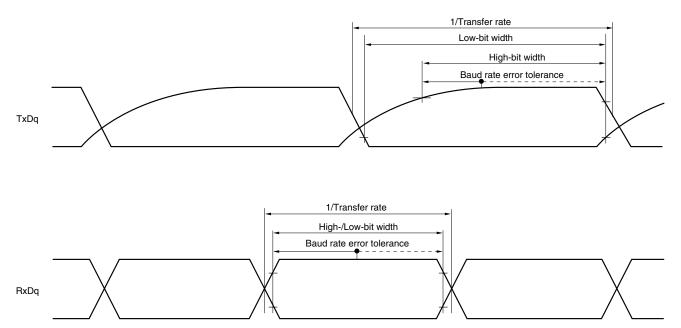
- $1.8~\text{V} \leq \text{EV}_\text{DD0} < 2.4~\text{V}$: MAX. 1.3 Mbps
- $1.6~V \leq EV_{\text{DD0}} < 1.8~V$: MAX. 0.6 Mbps
- 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

 $\begin{array}{lll} \text{HS (high-speed main) mode:} & 32 \ \text{MHz} \ (2.7 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ & 16 \ \text{MHz} \ (2.4 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ \text{LS (low-speed main) mode:} & 8 \ \text{MHz} \ (1.8 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ \text{LV (low-voltage main) mode:} & 4 \ \text{MHz} \ (1.6 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}) \\ \end{array}$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).



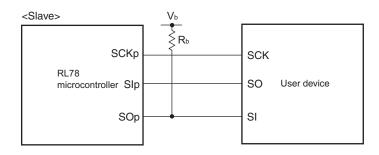




- **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- **3.** fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
- **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.



CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fмск: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



Parameter	Symbol	Conditions	HS (higl main)		``	r-speed Mode		-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat		1/fмск + 135 ^{Note 3}		1/fмск + 190 _{Note 3}		1/fмск + 190 _{Note 3}		kHz
		$\label{eq:V} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 135 ^{Note 3}		1/fмск + 190 _{Note 3}		1/fмск + 190 _{Note 3}		kHz
			1/fмск + 190 ^{Note 3}		1/fмск + 190 _{Note 3}		1/fмск + 190 _{Note 3}		kHz
		$\label{eq:linear} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 190 ^{Note 3}		1/fмск + 190 _{Note 3}		1/fмск + 190 _{Note 3}		kHz
		$ \begin{split} & 1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ & C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split} $	1/f _{MCK} + 190 ^{Note 3}		1/fмск + 190 _{Note 3}		1/fмск + 190 _{Note 3}		kHz
Data hold time (transmission)	thd:dat	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	305	0	305	0	305	ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	305	0	305	0	305	ns
			0	355	0	355	0	355	ns
		$\label{eq:linear} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	355	0	355	0	355	ns
		$\label{eq:VDD} \begin{split} & 1.8 \ V \leq EV_{\text{DD0}} < 3.3 \ V, \\ & 1.6 \ V \leq V_{\text{b}} \leq 2.0 \ V^{\text{Note 2}}, \\ & C_{\text{b}} = 100 \ \text{pF}, \ R_{\text{b}} = 5.5 \ \text{k}\Omega \end{split}$	0	405	0	405	0	405	ns

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2) (T_A = -40 to +85°C. 1.8 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V. Vss = EV_{SS0} = EV_{SS1} = 0 V)

Notes 1. The value must also be equal to or less than f_MCK/4.

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)



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Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -3.0 \ mA \end{array}$	EV _{DD0} - 0.7			V
		to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Ioh1 = -2.0 mA	EV _{DD0} - 0.6			V
		P117, P120, P125 to P127, P130, P140 to P147	$\begin{array}{l} 2.4 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -1.5 \ mA \end{array}$	EV _{DD0} - 0.5			V
	Vон2	P20 to P27, P150 to P156	2.4 V \leq V _{DD} \leq 5.5 V, Іон ₂ = -100 μ А	Vdd - 0.5			V
Output voltage, low	Vol1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 8.5 \ mA \end{array} \end{array} \label{eq:eq:optimal_decay}$			0.7	V
	P90 to P9	to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130,	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 3.0 \ mA \end{array} \end{array} \label{eq:eq:electropy}$			0.6	V
		P140 to P147	$eq:local_$			0.4	V
			$eq:local_$			0.4	V
	Vol2	P20 to P27, P150 to P156	$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $\text{Iol2} = 400 \ \mu \text{ A}$			0.4	V
	Vol3	P60 to P63	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OL3}} = 15.0 \ mA \end{array}$			2.0	V
			$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ \\ I_{\text{OL3}} = 5.0 \ mA \end{array}$			0.4	V
			$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ I_{\text{OL3}} = 3.0 \ mA \end{array}$			0.4	V
			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OL3}} = 2.0 \text{ mA}$			0.4	V

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (4/5)

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply current Note 1		Operating mode	HS (high- speed main) mode ^{Note 5}	fi⊢ = 32 MHz ^{№te 3}	Basic operatio n	V _{DD} = 5.0 V V _{DD} = 3.0 V		2.3 2.3		mA mA
					Normal operatio	V _{DD} = 5.0 V V _{DD} = 3.0 V		5.2 5.2	9.2 9.2	mA mA
				fin = 24 MHz ^{Note 3}	n Normal operatio	V _{DD} = 5.0 V V _{DD} = 3.0 V		4.1 4.1	7.0 7.0	mA mA
				fін = 16 MHz ^{№оtе 3}	n Normal	$V_{DD} = 5.0 V$		3.0	5.0	mA
					operatio n	$V_{DD} = 3.0 V$		3.0	5.0	mA
			HS (high- speed main) mode ^{Note 5}	$f_{MX} = 20 \text{ MHz}^{Note 2},$	Normal operatio n	Square wave input		3.4	5.9	mA
				V _{DD} = 5.0 V		Resonator connection		3.6	6.0	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$ $V_{DD} = 3.0 \text{ V}$	Normal operatio n	Square wave input Resonator		3.4 3.6	5.9 6.0	mA mA
			fмx = 10 MHz ^{Note 2} ,	Normal	connection Square wave input		2.1	3.5	mA	
		V DD = 0.0 V	operatio n	Resonator connection		2.1	3.5	mA		
			$f_{MX} = 10 \text{ MHz}^{Note 2},$	- · ·	Square wave input		2.1	3.5	mA	
			V _{DD} = 3.0 V	operatio n	Resonator connection		2.1	3.5	mA	
			Subsystem clock operation	fsub = 32.768 kHz	Normal operatio	Square wave input Resonator		4.8	5.9	μA
				T _A = -40°C	n	connection		4.9	6.0	μA
				fsub = 32.768 kHz Note 4	Normal operatio	Square wave input Resonator		4.9 5.0	5.9 6.0	μA μA
	fsL Note	$T_A = +25^{\circ}C$	n Nama l	connection		5.0	7.0			
		$f_{SUB} = 32.768 \text{ kHz}$ Note 4 $T_A = +50^{\circ}\text{C}$	Normal operatio n	Square wave input Resonator connection		5.0 5.1	7.6 7.7	μΑ μΑ		
			fsub = 32.768 kHz	Normal operatio n	Square wave input		5.2	9.3	μA	
			$T_A = +70^{\circ}C$		Resonator connection		5.3	9.4	μA	
				fsub = 32.768 kHz	Normal	Square wave input		5.7	13.3	μA
				T _A = +85°C	operatio n	Resonator connection		5.8	13.4	μA
		fsub = 32.76	fsub = 32.768 kHz	Normal operatio	Square wave input Resonator		10.0 10.0	46.0 46.0	μA μA	
				T _A = +105°C	n	connection		10.0	40.0	μη

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products	
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (1/2)	

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

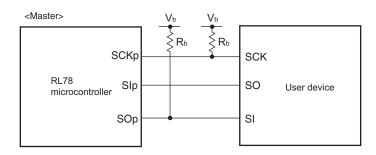
HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz

2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz

- **Remarks 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number , n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



3.5.2 Serial interface IICA

Parameter	Symbol	Conditions	HS (h	HS (high-speed main) Mode			Unit
				Standard Mode		Fast Mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fsc∟	Fast mode: fclk ≥ 3.5 MHz	-	-	0	400	kHz
		Standard mode: fclk ≥ 1 MHz	0	100	-	_	kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μS
Hold time ^{Note 1}	thd:sta		4.0		0.6		μS
Hold time when SCLA0 = "L"	t∟ow		4.7		1.3		μs
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μs
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μS
Setup time of stop condition	tsu:sto		4.0		0.6		μs
Bus-free time	t BUF		4.7		1.3		μs

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{ Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

<R>

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

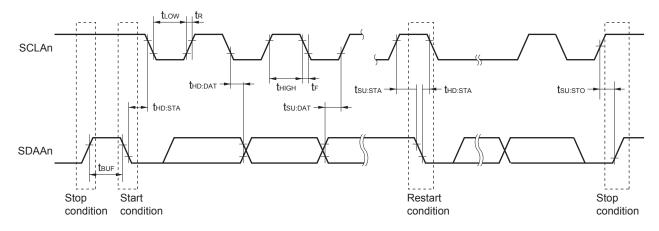
2. The maximum value (MAX.) of the:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

 $\begin{array}{ll} \mbox{Standard mode:} & C_b = 400 \mbox{ pF}, \mbox{ } R_b = 2.7 \mbox{ } k\Omega \\ \mbox{Fast mode:} & C_b = 320 \mbox{ pF}, \mbox{ } R_b = 1.1 \mbox{ } k\Omega \\ \end{array}$

IICA serial transfer timing







R5F100GAANA, R5F100GCANA, R5F100GDANA, R5F100GEANA, R5F100GFANA, R5F100GGANA, R5F100GHANA, R5F100GJANA, R5F100GKANA, R5F100GLANA

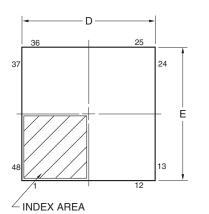
R5F101GAANA, R5F101GCANA, R5F101GDANA, R5F101GEANA, R5F101GFANA, R5F101GGANA, R5F101GHANA, R5F101GJANA, R5F101GKANA, R5F101GLANA

R5F100GADNA, R5F100GCDNA, R5F100GDDNA, R5F100GEDNA, R5F100GFDNA, R5F100GGDNA, R5F100GHDNA, R5F100GJDNA, R5F100GKDNA, R5F100GLDNA

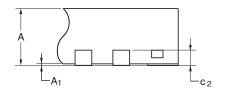
R5F101GADNA, R5F101GCDNA, R5F101GDDNA, R5F101GEDNA, R5F101GFDNA, R5F101GGDNA, R5F101GHDNA, R5F101GJDNA, R5F101GKDNA, R5F101GLDNA

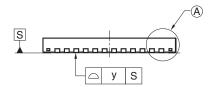
R5F100GAGNA, R5F100GCGNA, R5F100GDGNA, R5F100GEGNA, R5F100GFGNA, R5F100GGGNA, R5F100GJGNA, R5F100GJGNA

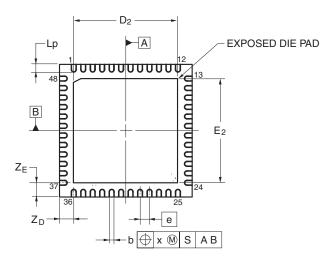
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]	
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-6		











Referance	Dimen	Dimension in Millimeters			
Symbol	Min	Nom	Max		
D	6.95	7.00	7.05		
E	6.95	7.00	7.05		
А			0.80		
A ₁	0.00		—		
b	0.18	0.25	0.30		
е		0.50			
Lp	0.30	0.40	0.50		
х			0.05		
у			0.05		
ZD		0.75			
Z _E		0.75			
C ₂	0.15	0.20	0.25		
D ₂		5.50			
E ₂		5.50			

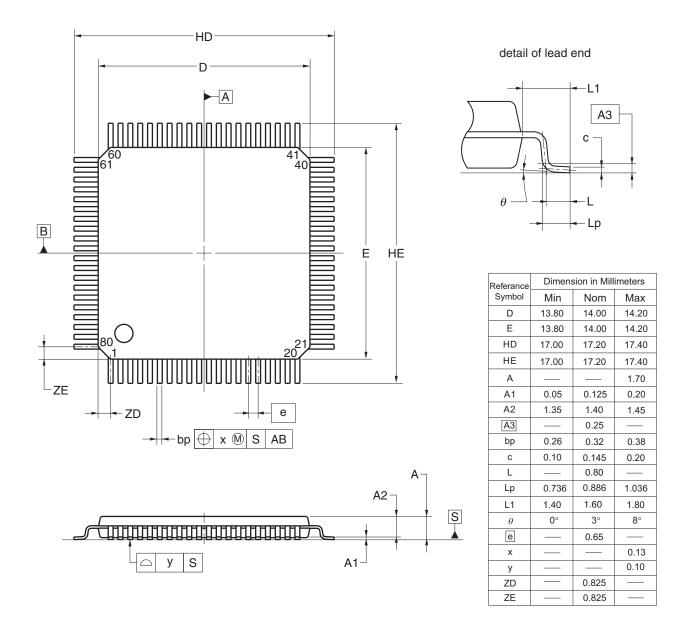
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4.12 80-pin Products

R5F100MFAFA, R5F100MGAFA, R5F100MHAFA, R5F100MJAFA, R5F100MKAFA, R5F100MLAFA R5F101MFAFA, R5F101MGAFA, R5F101MHAFA, R5F101MJAFA, R5F101MKAFA, R5F101MLAFA R5F100MFDFA, R5F100MGDFA, R5F100MHDFA, R5F100MJDFA, R5F100MKDFA, R5F100MLDFA R5F101MFDFA, R5F101MGDFA, R5F101MHDFA, R5F101MJDFA, R5F101MKDFA, R5F101MLDFA R5F100MFGFA, R5F100MGGFA, R5F100MHGFA, R5F100MJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69



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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.